

L Number	Hits	Search Text	DB	Time stamp
2	0	(w tungsten) adj2 (silicon si) adj2 (n nitride) near15 thick\$4 and semiconductor and (interconnect\$4 wiring wire\$ contact\$3)	USPAT; US-PGPUB; EPO; JPO	2004/10/12 13:52
3	2	(w tungsten) adj2 (silicon si) adj2 (n nitride) and semiconductor and (interconnect\$4 wiring wire\$ contact\$3)	USPAT; US-PGPUB; EPO; JPO	2004/10/12 13:55
4	2	((w tungsten) adj2 (silicon si) adj2 (n nitride) and semiconductor and (interconnect\$4 wiring wire\$ contact\$3)) and (w tungsten) adj2 (silicon si) adj2 (n nitride)	USPAT; US-PGPUB; EPO; JPO	2004/10/12 13:54
5	2408764	(w tungsten) adj\$4 (silicon si) adj\$4 (n nitride) and semiconductor and (interconnect\$4 wiring wire\$ contact\$3)	USPAT; US-PGPUB; EPO; JPO	2004/10/12 13:56
6	2408720	((w tungsten) adj\$4 (silicon si) adj\$4 (n nitride) and semiconductor and (interconnect\$4 wiring wire\$ contact\$3)) and (w tungsten) adj\$4 (silicon si) adj\$4 (n nitride) near15 thick\$4 and semiconductor and (interconnect\$4 wiring wire\$ contact\$3)	USPAT; US-PGPUB; EPO; JPO	2004/10/12 13:59
7	2339790	((w tungsten) adj\$4 (silicon si) adj\$4 (n nitride) and semiconductor and (interconnect\$4 wiring wire\$ contact\$3)) and (w tungsten) adj\$3 (silicon si) adj\$3 (n nitride) near15 thick\$4 and semiconductor and (interconnect\$4 wiring wire\$ contact\$3)	USPAT; US-PGPUB; EPO; JPO	2004/10/12 14:01
8	1973346	((w tungsten) adj\$4 (silicon si) adj\$4 (n nitride) and semiconductor and (interconnect\$4 wiring wire\$ contact\$3)) and (w tungsten) adj\$2 (silicon si) adj\$2 (n nitride) near15 thick\$4 and semiconductor and (interconnect\$4 wiring wire\$ contact\$3)	USPAT; US-PGPUB; EPO; JPO	2004/10/12 14:02
9	32598	((w tungsten) adj\$4 (silicon si) adj\$4 (n nitride) and semiconductor and (interconnect\$4 wiring wire\$ contact\$3)) and (w tungsten) adj\$2 (silicon si) adj\$2 (n nitride) near15 thick\$4 and semiconductor and (interconnect\$4 wiring wire\$ contact\$3)) and (tungsten adj silicon adj nitride\$1 w adj si adj\$2 n) near15 thick\$4	USPAT; US-PGPUB; EPO; JPO	2004/10/12 14:15
10	465	((w tungsten) adj\$4 (silicon si) adj\$4 (n nitride) and semiconductor and (interconnect\$4 wiring wire\$ contact\$3)) and (w tungsten) adj\$2 (silicon si) adj\$2 (n nitride) near15 thick\$4 and semiconductor and (interconnect\$4 wiring wire\$ contact\$3)) and (tungsten adj silicon adj nitride\$1 w adj si adj\$2 n) near15 thick\$4) and grad\$3 near5 (tungsten adj silicon adj nitride\$1 w adj si adj\$2 n)	USPAT; US-PGPUB; EPO; JPO	2004/10/12 14:06
11	465	((w tungsten) adj\$4 (silicon si) adj\$4 (n nitride) and semiconductor and (interconnect\$4 wiring wire\$ contact\$3)) and (w tungsten) adj\$2 (silicon si) adj\$2 (n nitride) near15 thick\$4 and semiconductor and (interconnect\$4 wiring wire\$ contact\$3)) and (tungsten adj silicon adj nitride\$1 w adj si adj\$2 n) near15 thick\$4) and grad\$3 near5 (tungsten adj silicon adj nitride\$1 w adj si adj\$2 n)) and grad\$3 near5 (tungsten adj silicon adj nitride\$1 w adj si adj\$2 n)	USPAT; US-PGPUB; EPO; JPO	2004/10/12 14:08

12	295	(((((w tungsten) adj\$4 (silicon si) adj\$4 (n nitride) and semiconductor and (interconnect\$4 wiring wire\$ contact\$3)) and (w tungsten) adj\$2 (silicon si) adj\$2 (n nitride) near15 thick\$4 and semiconductor and (interconnect\$4 wiring wire\$ contact\$3)) and (tungten adj silicon adj nitride\$1 w adj si adj\$2 n) near15 thick\$4) and grad\$3 near5 (tungten adj silicon adj nitride\$1 w adj si adj\$2 n)) and grad\$3 near3 (tungten adj silicon adj nitride\$1 w adj si adj\$2 n)	USPAT; US-PGPUB; EPO; JPO	2004/10/12 14:11
13	15	(((((w tungsten) adj\$4 (silicon si) adj\$4 (n nitride) and semiconductor and (interconnect\$4 wiring wire\$ contact\$3)) and (w tungsten) adj\$2 (silicon si) adj\$2 (n nitride) near15 thick\$4 and semiconductor and (interconnect\$4 wiring wire\$ contact\$3)) and (tungten adj silicon adj nitride\$1 w adj si adj\$2 n) near15 thick\$4) and grad\$3 near5 (tungten adj silicon adj nitride\$1 w adj si adj\$2 n)) and barrier near10 grad\$3 near3 (tungten adj silicon adj nitride\$1 w adj si adj\$2 n)	USPAT; US-PGPUB; EPO; JPO	2004/10/12 14:12
14	370021	((((w tungsten) adj\$4 (silicon si) adj\$4 (n nitride) and semiconductor and (interconnect\$4 wiring wire\$ contact\$3)) and (w tungsten) adj\$2 (silicon si) adj\$2 (n nitride) near15 thick\$4 and semiconductor and (interconnect\$4 wiring wire\$ contact\$3)) and grad\$7 (tungten adj silicon w adj si) near15 thick\$4	USPAT; US-PGPUB; EPO; JPO	2004/10/12 14:17
16	1434	(((((w tungsten) adj\$4 (silicon si) adj\$4 (n nitride) and semiconductor and (interconnect\$4 wiring wire\$ contact\$3)) and (w tungsten) adj\$2 (silicon si) adj\$2 (n nitride) near15 thick\$4 and semiconductor and (interconnect\$4 wiring wire\$ contact\$3)) and grad\$7 (tungten adj silicon w adj si) near15 thick\$4) and diffusion near3 (barrier prevent\$3) near7 grad\$7 (tungten adj silicon w adj si)	USPAT; US-PGPUB; EPO; JPO	2004/10/12 14:20
17	75	(((((w tungsten) adj\$4 (silicon si) adj\$4 (n nitride) and semiconductor and (interconnect\$4 wiring wire\$ contact\$3)) and (w tungsten) adj\$2 (silicon si) adj\$2 (n nitride) near15 thick\$4 and semiconductor and (interconnect\$4 wiring wire\$ contact\$3)) and grad\$7 (tungten adj silicon w adj si) near15 thick\$4) and diffusion near3 (barrier prevent\$3) near7 grad\$7 (tungten adj silicon w adj si)) and (tungten adj silicon w adj si) near7 nitrid\$5	USPAT; US-PGPUB; EPO; JPO	2004/10/12 14:31
19	0	(((((w tungsten) adj\$4 (silicon si) adj\$4 (n nitride) and semiconductor and (interconnect\$4 wiring wire\$ contact\$3)) and (w tungsten) adj\$2 (silicon si) adj\$2 (n nitride) near15 thick\$4 and semiconductor and (interconnect\$4 wiring wire\$ contact\$3)) and grad\$7 (tungten adj silicon w adj si) near15 thick\$4) and diffusion near3 (barrier prevent\$3) near7 grad\$7 (tungten adj silicon w adj si)) and (tungten adj silicon w adj si) near7 nitrid\$5) and grad\$3 near7 (tungten adj silicon w adj si) near7 nitrid\$5	USPAT; US-PGPUB; EPO; JPO	2004/10/12 14:32

20	0	((((w tungsten) adj\$4 (silicon si) adj\$4 (n nitride) and semiconductor and (interconnect\$4 wiring wire\$ contact\$3)) and (w tungsten) adj\$2 (silicon si) adj\$2 (n nitride) near15 thick\$4 and semiconductor and (interconnect\$4 wiring wire\$ contact\$3)) and grad\$7 (tungsten adj silicon w adj si) near15 thick\$4) and diffusion near3 (barrier prevent\$3) near7 grad\$7 (tungsten adj silicon w adj si)) and (tungsten adj silicon w adj si) near7 nitrid\$5) and grad\$5 near7 (tungsten adj silicon w adj si) near7 nitrid\$5	USPAT; US-PGPUB; EPO; JPO	2004/10/12 14:33
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